NSN 5962-01-037-8595

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Body Length:
0.896 inches
Body Width:
Between 0.220 inches and 0.310 inches
Body Height:
Between 0.140 inches and 0.185 inches
Maximum Power Dissipation Rating:
625.0 milliwatts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Hermetically sealed and monolithic and positive outputs and w/enable and programmable and programmed and w/decoded output and
w/storage and w/open collector and expandable and high speed and w/disable and w/buffered output
Inclosure Material:
Ceramic and glass
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
10 input
Case Outline Source And Designator:
D-2 mil-m-38510
Terminal Surface Treatment:
Solder
Voltage Rating And Type Per Characteristic:
5.5 volts power source
Time Rating Per Chacteristic:
70.00 nanoseconds propagation delay time, low to high level output and 70.00 nanoseconds propagation delay time, high to low level
output
Memory Device Type:
Rom
Test Data Document:
36659-xn1306416 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing
etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)
Terminal Type And Quantity:
16 printed circuit
Shelf Life:

Demilitarization:

Unit Of Measure:

N/a

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